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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										備考	
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αB} f _r * (Mc)		C _{ob} (pF)
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αB} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)										外 形	備 考				
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CE(V)}	直流又はパルス hFE	バイアス	h _{FE}	h _{FE} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μΩ)	f _{αβ} f _T * (Mc)			C _{ob} (pF)	τ _{bb} h _{ic} (real)* (Ω)		
★ 2SC683	日立	RF	Si.P	20	3	20	180	175	0.1	10	60	10	2	10	-2	75	PG = 21dB (f = 200Mc)	550*	C _{ob} 0.37	9	フワード AGC			
★ " 684	"	RF Conv. Mix Osc	Si.EP	30	2	50	200	125	0.5	10	>40	10	10	10	-10	50	P _{oss} = 8mW (f = 930Mc)	1100*	1.2	C _c τ _{bb} 10pS	37			
★ " 685	"	PA	Si.T	300	4	100	4W (T _c = 25°C)	150	5	150	60-120	10	50	10	-50			25*	5		153			
★ " 686	日電	RF	Si.E	150	6	50	800	175	0.01	100	90	10	25	10	-25	100		180*	2.6	10*	84B			
★ " 687	松下	SW	Si.EP	150	6	5A	50W (T _c = 25°C)	150	15mA	150	30	4	5A				t _r < 2 μS, t _f < 1 μS				102			
★ " 688	三菱	PA	"	60	4	1.5A	20W (T _c = 25°C)	200	500	25				10	-100	30	PG = 8.5dB (f = 150Mc, P _i = 1.9W)		20		114			
★ " 689	日立	SW	"	40	5	100	300	175	0.25	20	85	1	10	10	-10		t _{on} = 6.5nS, t _{off} = 8nS t _{sw} = 3nS	>600*	1.8		49C			
★ " 690	三菱	PA	"	60	5	3A	30W (T _c = 25°C)	175	500	30	50	10	100				P _o = 25W (f = 150MHz, V _{CC} = 25V, P _i = 5W)				113			
★ " 691	"	"	"	60	4	00	8.6W (T _c = 25°C)	175	200	30	50	10	100				P _o = 3.5W (f = 150MHz, V _{CC} = 24V, P _i = 0.3W)				113			
★ " 692	"	"	"	60	5	1A	15W (T _c = 25°C)	175	200	30	50	10	100				P _o = 9W (f = 150MHz, V _{CC} = 28V, P _i = 3W)				113			
★ " 693	三洋	RF.LN	Si.P	40	5	50	100	125	1	35	160-960	6	1	6	-1			100*	4		138			
★ " 694	"	"	"	40	5	50	100	125	1	35	160-960	6	1	6	-1			100*	4		138			
★ " 695	日電	AF.RF	Si.E	20	5	30	100	150	0.1	15	150	3	0.1	6	-1	200	6000	0.9	20	150*	2	50*	23	
★ " 696	松下	PA	Si.EP	100	5	3A	750	175	3	30	55	V _{CE} = 2V	100	2	-100	80		100*	20	C _c τ _{bb} 40pS	84B	2SA546 とコンパリ		
★ " 696A	"	"	"	130	5	3A	750	175	3	30	55	V _{CE} = 2V	100	2	-100	80		100*	20	C _c τ _{bb} 40pS	84B	2SA56A とコンパリ		
★ " 697	"	"	"	100	5	3A	10W (T _c = 25°C)	175	3	30	55	V _{CE} = 2V	100	2	-100	80		100*	22	C _c τ _{bb} 40pS	97B	2SA547 とコンパリ		
★ " 697A	"	"	"	130	5	3A	10W (T _c = 25°C)	175	3	30	55	V _{CE} = 2V	100	2	-100	80		100*	22	C _c τ _{bb} 40pS	97B	2SA57A とコンパリ		
★ " 698	日電	RF.PA	Si.E	100	5	3A	10W (T _c = 25°C)	175	1	60	80	2	0.5A	10	-50	85			90*	35	15*	97B		
★ " 699	三菱	PA	Si.TP	50	4	1A	10W (T _c = 25°C)	200	50	12				12	-100	30	PG = 9dB (f = 27MHz, P _i = 0.5W)		20		97B			
★ " 700	"	"	Si.EP	60	3	500	5W (T _c = 25°C)	200	100	20				20	-50	30	PG = 11dB (f = 150MHz, P _i = 0.2W)		6		84C			
★ " 701	"	"	"		3	750	5W (T _c = 25°C)	200	100	15				15	-50	30	PG = 10dB (f = 150MHz, P _i = 0.2W)		7		84C			
★ " 702	"	"	"	40	4	750	8.6W (T _c = 25°C)	175	100	15	50	10	100				P _o = 3W (f = 150MHz, V _{CC} = 15V, P _i = 0.25W)				113			
★ " 703	"	"	"	40	5	2A	21W (T _c = 25°C)	175	1mA	15	50	10	100				P _o = 12W (f = 175MHz, V _{CC} = 13.5V, P _i = 3.5W)				113			
★ " 704	"	"	"	40	5	4A	34W (T _c = 25°C)	175	2mA	15	50	10	100				P _o = 17W (f = 175MHz, V _{CC} = 13.5V, P _i = 5.5W)				113			
★ " 705	三洋	RF Conv. Mix. Osc.	"	15	3	30	120	125	1	10	70	6	1	6	-1			700*	1.5	C _c τ _{bb} 14pS	27			
★ " 706	"	RF	"	15	3	30	120	125	1	10	80	6	1	6	-1			800*	1.1	C _c τ _{bb} 17pS	27			
★ " 707	日立	RF	Si.P	20	3	20	150	175	0.1	10	50	10	2	10	-2	75	PG = 12dB (f = 800MHz)	650*	0.4		9			
★ " 708	"	SW	Si.T	60	4	1A	750	150	10	30	30-160	4	50	4	-30			15*	25		84B	2SA537 とコンパリ		
★ " 708A	"	"	"	100	4	1A	750	150	10	30	30-160	4	50	4	-30			15*	25		84B	2SA537A とコンパリ		
★ " 709	三菱	RF Conv Mix. Osc	Si.EP	25	4	100	200	125	1	25	75	6	10	6	-1	60		180*	3.5	C _c τ _{bb} 180pS	138B			